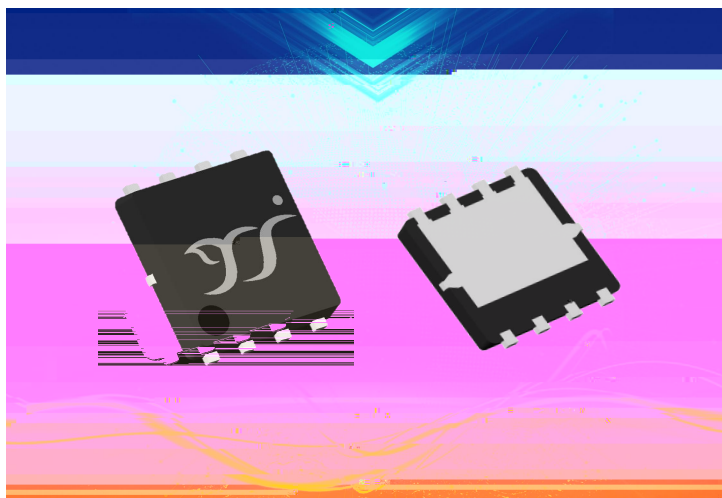


NEW
PRODUCT

New N100V MOSFET for PD Power Supply

Product
Features

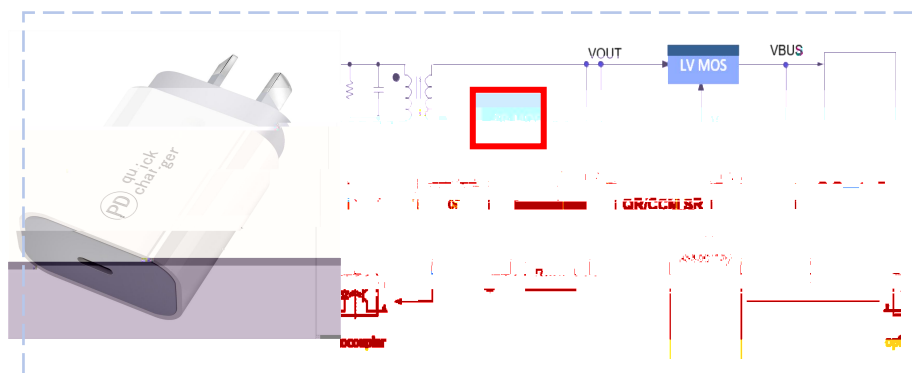


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YangJie technology recently launched a series of N100V mosfet products for PD power supplies. The products adopt specially optimized SGT technology, with low $R_{ds(on)}$ and Q_g , significantly reducing forward voltage drop and switching losses while enhancing the avalanche resistance of the mosfet.

1. The product utilizes optimized SGT technology, featuring low on-resistance and excellent switching performance.
2. The product adopts PDFN 5*6-8L package, suitable for PD power synchronous rectifier applications
3. For various working states of power supply applications, optimize the EAS capability of MOS products to enhance their reliability.

Product Name	Package	Vds V	ID A	Vth V typ.	Rds10V mohm typ.	Rds10V mohm max.	Qg10V nC typ.	Tj	N/P
YJG8D0G10H	PDFN5060-8L	100	83	3	6.3	8	22.7	-55-150	N
YJG7D4G10H	PDFN5060-8L	100	86	3	6.1	7.4	23.4	-55-150	N
YJG6D3G10H	PDFN5060-8L	100	100	3	5.1	6.3	26.3	-55-150	N
YJG5D2G10H	PDFN5060-8L	100	105	3	4.3	5.2	35.8	-55-150	N
YJG4D6G10H	PDFN5060-8L	100	149	3	3.7	4.6	40.2	-55-150	N



Typical
Applica-
-tions

Power Delivery charger